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*D1003

*PSPICE MODEL FOR POINT NINE RF N-CHANNEL VERTICAL DMOS POWER FET
*May 2004


*                  ____GATE
*                  I   ____DRAIN
*                  I   I   ____SOURCE
*                  I   I   I
.SUBCKT D1003  10  20  30
Cin1,Cin2 & Lin model the input side of the package
Cin1   10    30    0.45p
Lin    10    11    0.68n
Cin2   11    30    0.45p
LG     11    12    1n    ;Gate bond wire inductance
CGS    12    13    138p  ;Gate-source capacitance
MOS    14    12    13    13  D1003 L=0.9U W=0.168    ;D G S B LEVEL1
JFET   16    13    14    D1003                       ;D G S
DBODY  13    16    D1003                             ;P N
LS     13    30    0.5n  ;Source bond wire inductance
CGD    12    16    3p    ;Gate-drain feedback capacitance

Cout1,Cout2 & Lout model the output side of the package
Cout1   16    30    1.2p
Lout    16    20    1.68n
Cout2   20    30    1.2p

.MODEL D1003  NMOS (VTO=4.76 KP=2.811E-5 LAMBDA=0.032 RD=0.025 RS=0.102)
 MODEL D1003  NJF  (VTO=-4.3 BETA=0.75 LAMBDA=0.54)
.MODEL D1003  D    (CJO=246.6P RS=0.25 VJ=0.7 M=0.35 BV=75)
.MODEL D1003  D    (CJO=246.6P RS=0.25 VJ=0.7 M=0.35 BV=75)

.ENDS
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